

PNP SILICON AMPLIFIER TRANSISTOR

Qualified per MIL-PRF-19500/357

Devices

2N3634	2N3635	2N3636	2N3637
2N3634L	2N3635L	2N3636L	2N3637L

Qualified Level

JAN
JANTX
JANTXV
JANS

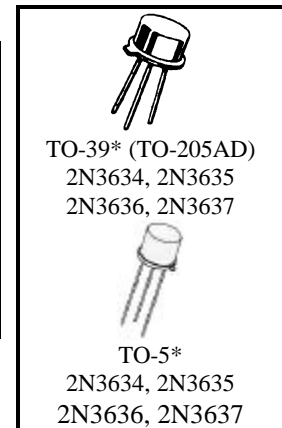
MAXIMUM RATINGS

Ratings	Symbol	2N3634* 2N3635*	2N3636* 2N3637*	Unit
Collector-Emitter Voltage	V_{CEO}	140	175	Vdc
Collector-Base Voltage	V_{CBO}	140	175	Vdc
Emitter-Base Voltage	V_{EBO}	5.0		Vdc
Collector Current	I_C	1.0		Adc
Total Power Dissipation	P_T	@ $T_A = +25^{\circ}C^{(1)}$	1.0	W
		@ $T_C = +25^{\circ}C^{(2)}$	5.0	W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^{\circ}C$

*Electrical characteristics for "L" suffix devices are identical to the "non L" corresponding devices

1) Derate linearly 5.71 mW/ $^{\circ}C$ for $T_A > +25^{\circ}C$

2) Derate linearly 28.6 mW/ $^{\circ}C$ for $T_C > +25^{\circ}C$



*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
-----------------	--------	------	------	------

OFF CHARACTERISTICS

Collector-Emitter Breakdown Current $I_C = 10$ mAdc	2N3634, 2N3635 2N3636, 2N3637	$V_{(BR)CEO}$	140 175	Vdc
Collector-Base Cutoff Current $V_{CB} = 100$ Vdc $V_{CB} = 140$ Vdc	2N3634, 2N3635	I_{CBO}	100 10	η Adc μ Adc
Emitter-Base Cutoff Current $V_{EB} = 3.0$ Vdc $V_{EB} = 5.0$ Vdc		I_{EBO}	50 10	η Adc μ Adc
Collector-Emitter Cutoff Current $V_{CE} = 100$ Vdc		I_{CEO}	10	μ Adc



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.